

Title (en)

METHOD OF TRIMMING THIN METAL RESISTORS

Publication

EP 0055331 A3 19830518 (EN)

Application

EP 81107584 A 19810923

Priority

US 22169580 A 19801231

Abstract (en)

[origin: EP0055331A2] A thin metal film resistor (15) of a capacitive graphic tablet is trimmed to make the resistor linear within about 0.25%. Alternating voltage is applied along the resistor by a source (40). The resistance of the resistor is measured at discrete points by a capacitive probe (34) and the resistance readings are stored in a data processor (45). A profile is calculated in the processor from the stored readings and a trim operation is made by an electro-erosion apparatus.

IPC 1-7

H01C 17/22; G06K 11/06

IPC 8 full level

G01R 27/02 (2006.01); **H01C 17/22** (2006.01); **H01C 17/24** (2006.01)

CPC (source: EP)

H01C 17/22 (2013.01); **H01C 17/2408** (2013.01)

Citation (search report)

- [A] DE 2344504 A1 19750313 - SIEMENS AG
- [A] GB 1149775 A 19690423 - ASSOCIATED SEMICONDUCTOR MFT [GB]
- [AD] US 4087625 A 19780502 - DYM HERBERT, et al
- [AD] FR 2376399 A1 19780728 - IBM [US]
- [A] IBM TECHNICAL DISCLOSURE BULLETIN, vol. 23, no. 2, July 1980, pages 666-667, New York (USA);

Designated contracting state (EPC)

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DOCDB simple family (publication)

EP 0055331 A2 19820707; **EP 0055331 A3 19830518**; **EP 0055331 B1 19850515**; DE 3170519 D1 19850620; JP S57121201 A 19820728; JP S6117124 B2 19860506

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